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Total No. of Questions: 09

B.Tech.(EE) PT (Sem.-3)
DIGITAL ELECTRONICS
Subject Code: BTEE-404
M.Code: 72164

Time: 3 Hrs. Max. Marks: 60

INSTRUCTION TO CANDIDATES:

- SECTION-A is COMPULSORY consisting of TEN questions carrying TWO marks each.
- SECTION-B contains FIVE questions carrying FIVE marks each and students has to attempt any FOUR questions.
- SECTION-C contains THREE questions carrying TEN marks each and students has to attempt any TWO questions.

SECTION-A

Answer briefly :

- a) What is the difference between a latch and a flip-flop?
- b) How do you specify the delay in VHDL?
- c) What is meant by a bit?
- d) Which gates are called as universal gates and what are their advantages?
- e) What are the fundamental properties of Boolean algebra?
- f) What are minterm and maxterm?
- g) What are the limitations of the Karnaugh map?
- h) What do we need to generate hardware from VHDL model?
- Write down the duality theorem.
- j) What is meant by Checksum?



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SECTION-B

- Explain interface between TTL to CMOS circuit.
- Design a 4-bit BCD adder using full adder and explain its structure and compute the circuit to add 1001 and 0101. Write the sum and carry outputs of the given binary number.
- 4. Select a 4096 × 8 bit ROM memory to store a program. The memory chip has two chip select inputs and operates from a 5V d.c. power supply. How many pins are needed for the integrated circuit package? Draw a neat block diagram and label all the input and the output terminals in the ROM.
- Design a 5 × 32 decoder using 3 × 8 decoder and summarize how many decoders are required for designing the circuit.
- Explain the organization of ROM with suitable diagrams.

SECTION-C

- A 5-bit D/A converter produces V_{OUT} = 0.2V for, a digital input of 0001. Find the value of V_{out} for an input of 11111.
- Write a program to implement a BCD to Excess-3 code conversion using a PLA.
- Explain in detail about the working of bipolar SRAM cell and single transistor DRAM cell with neat sketches.

NOTE: Disclosure of Identity by writing Mobile No. or Making of passing request on any page of Answer Sheet will lead to UMC against the Student.

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